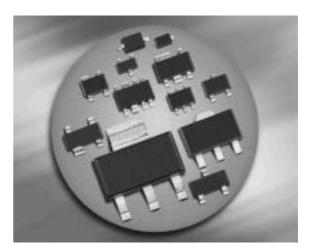


Silicon Switching Diode

- For high-speed switching applications
- Pb-free (RoHS compliant) package¹⁾
- Qualified according AEC Q101





BAL74

BAR74





Туре	Package	Configuration	Marking
BAL74	SOT23	single	JCs
BAR74	SOT23	single	JBs

Maximum Ratings at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit	
Diode reverse voltage	V _R	50	V	
Peak reverse voltage	V _{RM}	50		
Forward current	I _F	250	mA	
Peak forward current	I _{FM}	-		
Surge forward current, $t = 1 \ \mu s$	I _{FS}	4.5	А	
Non-repetitive peak surge forward current	I _{FSM}	-		
Total power dissipation	P _{tot}	370	mW	
$T_{S} \leq 54^{\circ}C$				
Junction temperature	Tj	150	°C	
Storage temperature	T _{stg}	-65 150		

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾ , BAL74, BAR74	R _{thJS}	≤ 260	K/W

¹Pb-containing package may be available upon special request

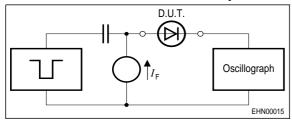
²For calculation of $R_{\rm thJA}$ please refer to Application Note Thermal Resistance



Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics	1	1			
Breakdown voltage	V _(BR)	50	-	-	V
<i>I</i> _(BR) = 100 μA					
Reverse current	I _R				μA
$V_{R} = 50 \text{ V}$		-	-	0.1	
$V_{\rm R} = 50 \text{ V}, \ T_{\rm A} = 150 \text{ °C}$		-	-	100	
Forward voltage	V _F	-	-	1	V
<i>I</i> _F = 100 mA					
AC Characteristics					
Diode capacitance	CT	-	-	2	pF
$V_{R} = 0 V, f = 1 MHz$					
Reverse recovery time	<i>t</i> _{rr}	-	-	4	ns
$I_{\rm F}$ = 10 mA, $I_{\rm R}$ = 10 mA, measured at $I_{\rm R}$ = 1mA,					
$R_{\rm L} = 100 \ \Omega$					

Electrical Characteristics at $T_{\Delta} = 25^{\circ}$ C, unless otherwise specified

Test circuit for reverse recovery time

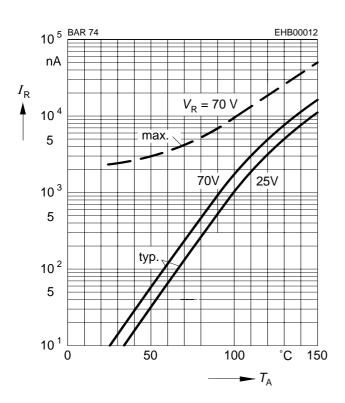


Pulse generator: t_p = 100ns, D = 0.05, t_r = 0.6ns, R_i = 50 Ω Oscillograph: R = 50 Ω , t_r = 0.35ns,



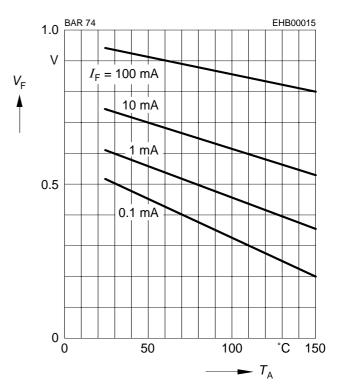
Reverse current $I_{R} = f(T_{A})$

 $V_{\rm R}$ = Parameter

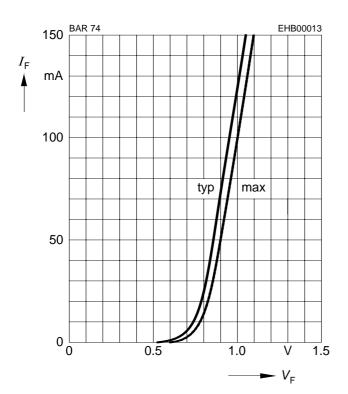


Forward Voltage $V_{\rm F} = f(T_{\rm A})$

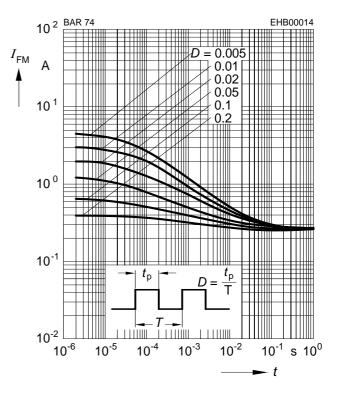
 $I_{\rm F}$ = Parameter



Forward current $I_{\rm F} = f (V_{\rm F})$



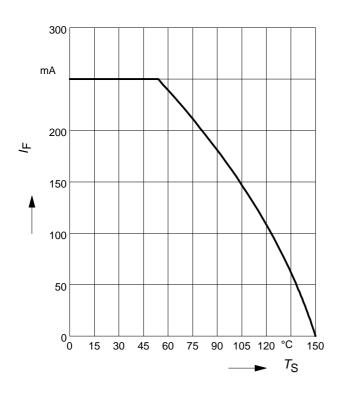
Peak forward current $I_{FM} = f(t_p)$



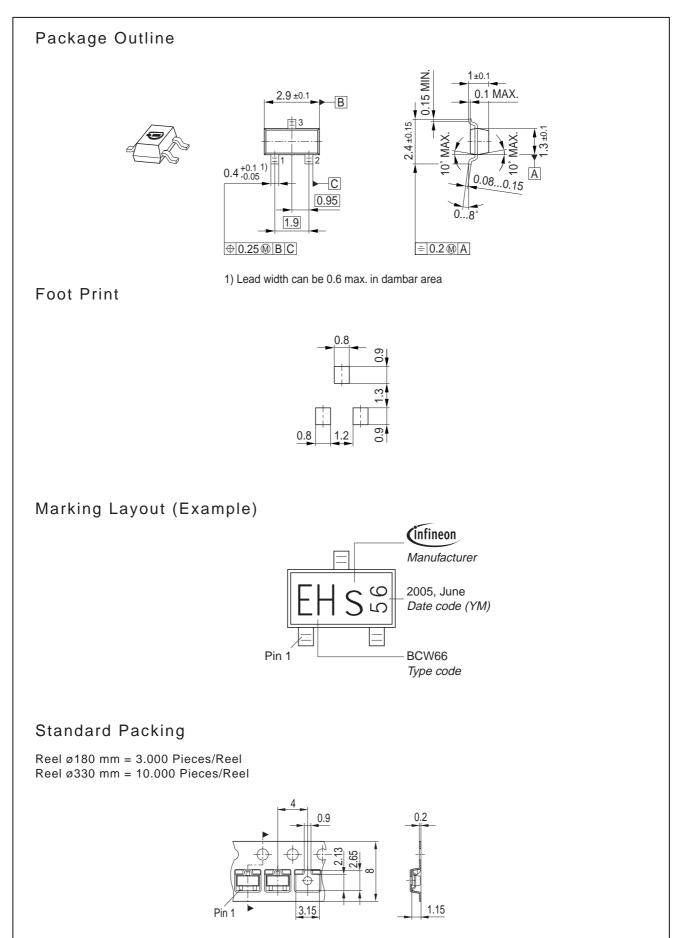


Forward current $I_{\rm F} = f(T_{\rm S})$

BAL74, BAR74









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